



# DATA SHEET

SEMICONDUCTOR

RB751CS-40

## SCHOTTKY BARRIER DIODE



### ●Applications

Low current rectification

### ●Features

Extremelysmall surface mounting type. (SOD923)

Low  $V_F$

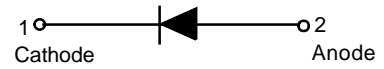
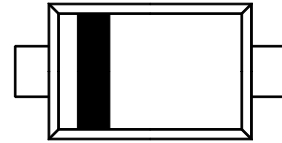
High reliability.

We declare that the material of product compliance with RoHS requirements.

### ●Construction

Silicon epitaxial planar

SOD-923



### DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB751CS-40	5	8000/Tape&Reel

### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	$V_{RM}$	40	V
Reverse voltage (DC)	$V_R$	30	V
Average rectified forward current	$I_o$	30	mA
Forward current surge peak (60Hz·1cyc)	$I_{FSM}$	200	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

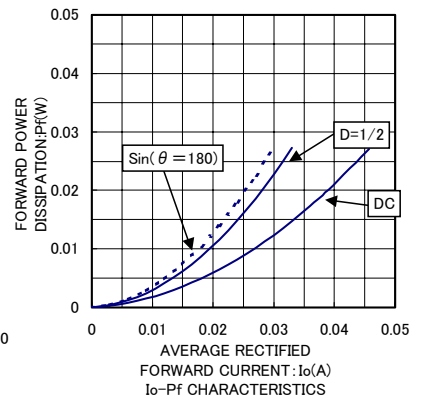
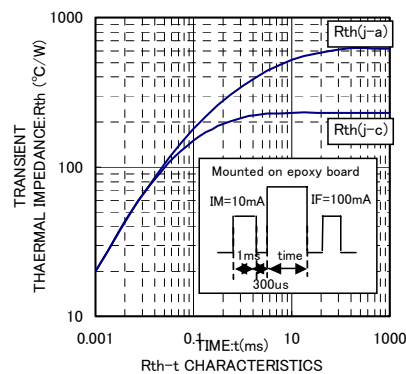
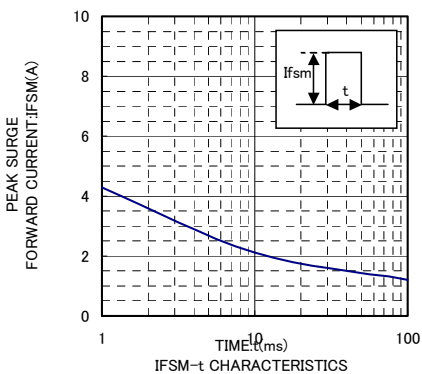
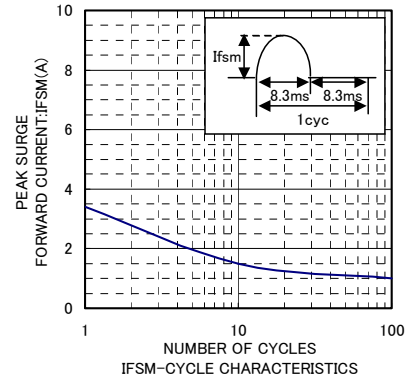
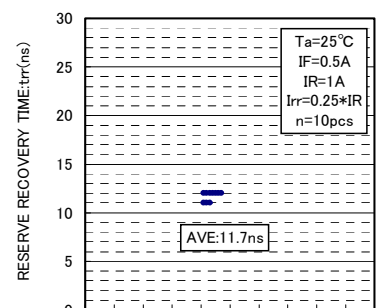
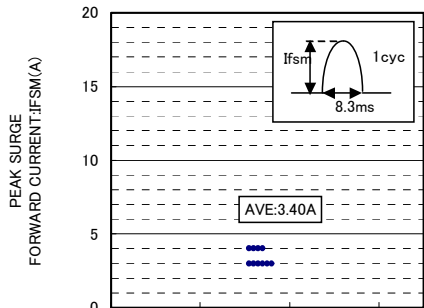
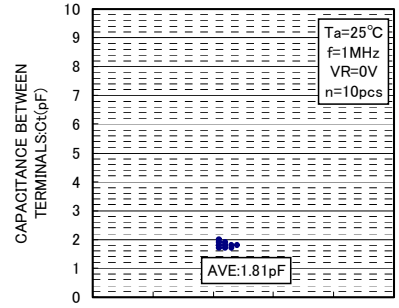
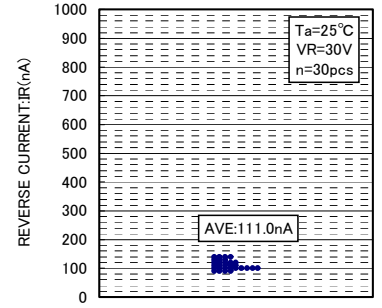
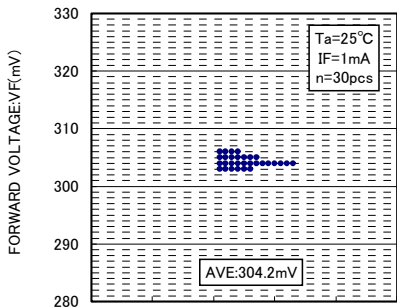
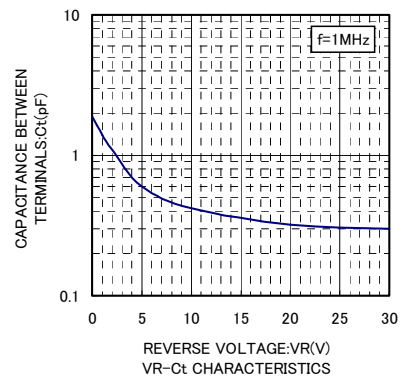
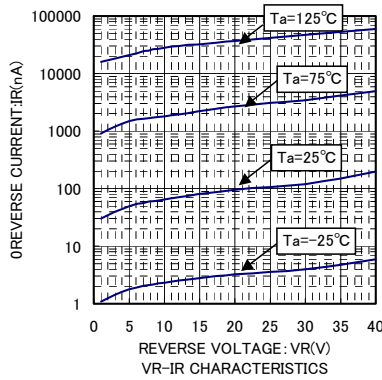
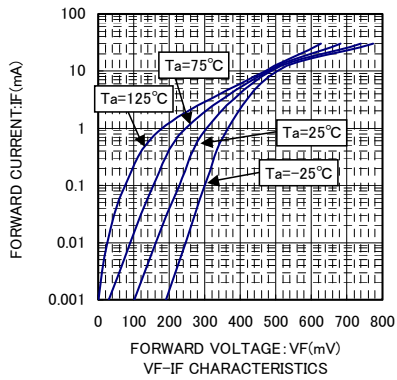
### ●Electrical characteristic (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-		0.37	V	$I_F=1mA$
Reverse current	$I_R$	-		0.5	$\mu A$	$V_R=30V$
Capacitance between terminals	$C_t$	-	2	-	pF	$V_R=1V, f=1MHz$

# DEVICE CHARACTERISTICS

## RB751CS-40

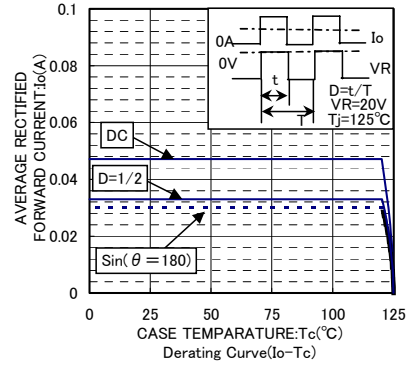
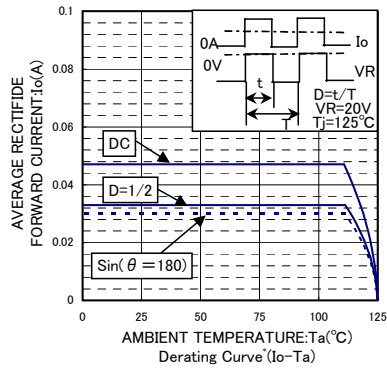
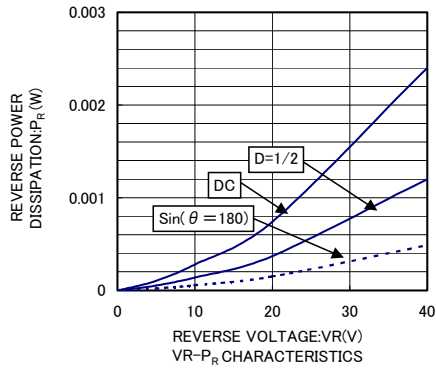
### ●Electrical characteristic curves



# DEVICE CHARACTERISTICS

## RB751CS-40

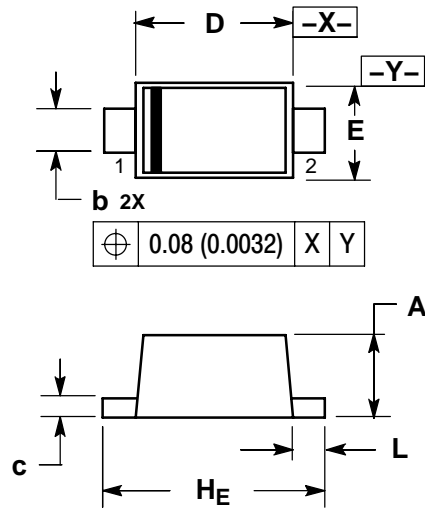
### Electrical characteristic curves ( $T_a=25^{\circ}\text{C}$ )



# PACKAGE OUTLINE & DIMENSIONS

## RB751CS-40

### SOD-923



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
<b>A</b>	0.34	0.39	0.43	0.013	0.015	0.017
<b>b</b>	0.15	0.20	0.25	0.006	0.008	0.010
<b>c</b>	0.07	0.12	0.17	0.003	0.005	0.007
<b>D</b>	0.75	0.80	0.85	0.030	0.031	0.033
<b>E</b>	0.55	0.60	0.65	0.022	0.024	0.026
<b>HE</b>	0.95	1.00	1.05	0.037	0.039	0.041
<b>L</b>	0.05	0.10	0.15	0.002	0.004	0.006